

General Description

The CMSC019N03LS is designed to provide a high efficiency synchronous buck power stage with optimal layout and board space utilization. This device is well suited for use in compact DC/DC converter applications.

Features

- Low ON-resistance
- 100% EAS Guaranteed
- Surface Mount Package
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current	50	A
$I_D@T_C=100^\circ C$	Continuous Drain Current	39	A
I_{DM}	Pulsed Drain Current	200	A
EAS	Single Pulse Avalanche Energy ¹	420	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation	83	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient(Device on PCB)	---	60	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-case	---	1.8	$^\circ C/W$

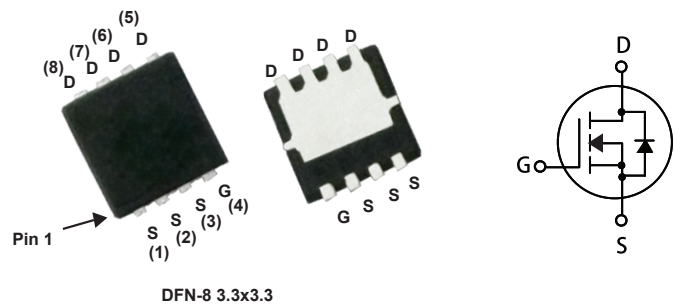
Product Summary

BVDSS	RDSON	ID
30V	1.9m Ω	50A

Applications

- Load switch, battery switch in portable devices

DFN-8 3.3x3 .3 Pin Configuration



Type	Package	Marking
CMSC019N03LS	DFN-8 3.3x3.3	019N03L

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=30A$	---	1.5	1.9	m Ω
		$V_{GS}=4.5V, I_D=20A$	---	2.1	2.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=20A$	---	48	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	3.5	---	Ω
Q_g	Total Gate Charge	$V_{DD}=15V, I_D=30A$ $V_{GS}=0$ to $4.5V$	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	7	---	
Q_{gd}	Gate-Drain Charge		---	6.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=1.6\Omega$ $I_D=30A$	---	6	---	ns
T_r	Rise Time		---	8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	30	---	
T_f	Fall Time		---	5	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	2400	---	pF
C_{oss}	Output Capacitance		---	720	---	
C_{rss}	Reverse Transfer Capacitance		---	80	---	

Diode Characteristics

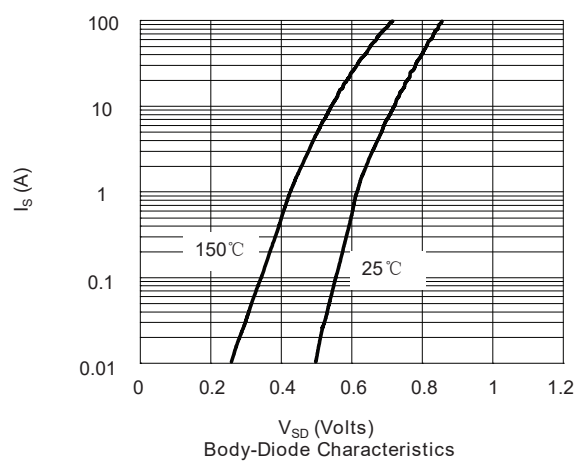
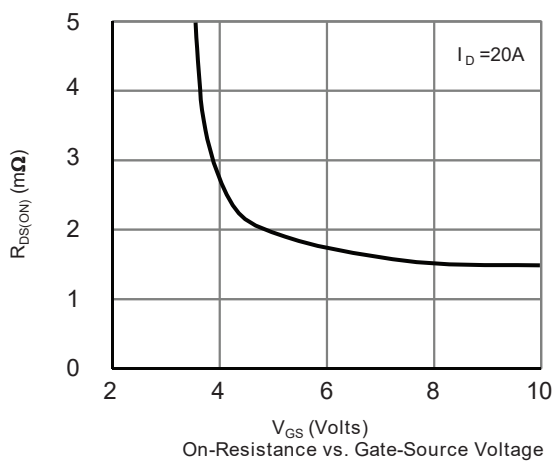
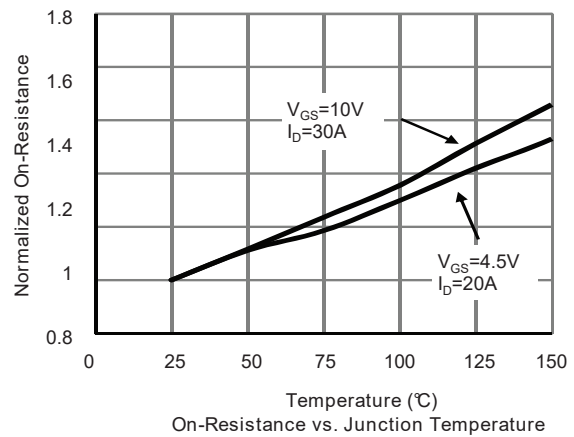
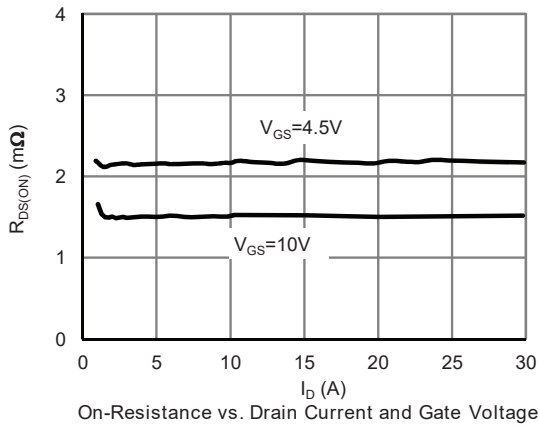
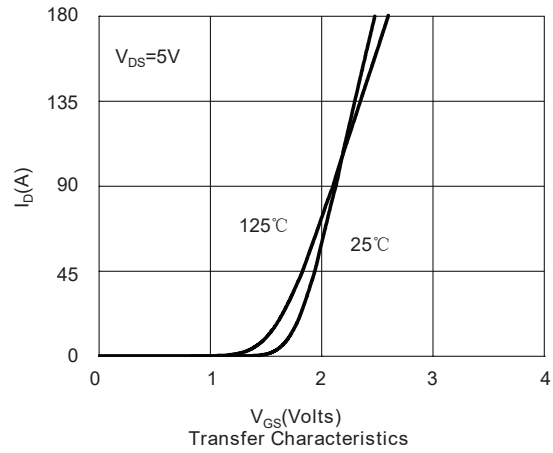
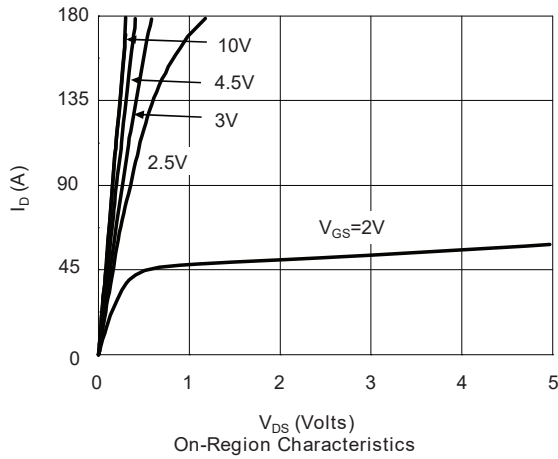
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0V$, Force Current	---	---	50	A
$I_{S,pulse}$	Diode pulse current		---	---	200	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=20A, T_J=25^{\circ}\text{C}$	---	0.75	1	V

Notes:

1.The EAS data shows Max. rating .The test condition is $V_{DS}=25V, V_{GS}=10V, L=0.5\text{mH}, I_{AS}=41A$.

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Cmos assumes no liability for customers' product design or applications.
Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics



Typical Characteristics

